Code: EC5T5

## III B.Tech - I Semester – Regular/Supplementary Examinations March 2021

## DIGITAL IC APPLICATIONS (ELECTRONICS & COMMUNICATION ENGINEERING)

Duration: 3 hours Max. Marks: 70

PART - A

Answer all the questions. All questions carry equal marks

11x 2 = 22 M

- 1. a) What is the difference between initial and always blocks?
  - b) Discuss the differences between blocking and non-blocking statements.
  - c) Explain the syntax of any two System Tasks with an example.
  - d) Compare CMOS and TTL families with respect to any two characteristics.
  - e) Define a propagation delay time of a gate.
  - f) Draw the logic diagram of IC 74x138.
  - g) Write the typical symbols of four Tri state gates.
  - h) What is the difference between latch and flip-flop?
  - i) What is a race around condition?
  - j) Write down the applications of ROM.
  - k) What are the advantages of two-dimensional decoding in ROM?

## PART - B

Answer any *THREE* questions. All questions carry equal marks.  $3 \times 16 = 48 \text{ M}$ 

- 2. a) Discuss different steps of design flow in VLSI. 8 M
  - b) Explain the following terms relevant to Verilog HDL. 8 M i) Module ii) Test bench
- 3. a) Discuss the factors to be considered for CMOS/TTL Interfacing. 8 M
  - b) Construct a CMOS 4-input AND-OR-INVERT gate and explain its operation with function table. 8 M
- 4. Illustrate an 8x1 multiplexer and write a behavioral level description along with a test bench and simulation results using Verilog HDL.

  16 M
- 5. a) Design a 4-bit up/down counter and write a behavioral level description using Verilog HDL. 8 M
  - b) Write a Verilog code for 4-bit bi-directional shift register using behavior level modeling style. 8 M
- 6. a) What is a ROM? Explain the internal ROM structure with logic diagram of 8x4 diode ROM. 8 M
  - b) Distinguish PROM, EPROM and EEPROM technologies. 8 M